Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A photothermographic material containing, on a substrate, at least a photosensitive silver halide having an average particle size of 5 nm to 40 nm, a non-photosensitive organic silver salt comprising silver behenate in an amount of 40 mol% to 99 mol%, a reducing agent and a binder, in which the total silver iodide content of the photosensitive silver halide is 40 mol% to or more and 100 mol% or less, and the coating amount of photosensitive silver halide in terms of an amount of silver is 0.0005 0.005 g/m² to or more and 0.4 0.05 g/m² or less wherein the photosensitive silver halide is formed in a state where the non-photosensitive organic salt is not present.

2. (cancelled)

3. (currently amended) A photothermographic material according to claim 1, wherein the total silver iodide content is 90 mol% or more and to 100 mol% of less.

4. (cancelled)

- 5. (cancelled)
- 6. (cancelled)
- 7. (original) A photothermographic material according to claim 1, wherein the reducing agent contains a compound represented by the general formula (R):

 General formula (R)

in which R^{11} and $R^{12'}$ each represents independently an alkyl group of 1 to 20 carbon atoms, R^{12} and $R^{12'}$ each represents independently an alkyl group of 1 to 20 carbon atoms, L represents an -S- group or -CHR¹³- group, R^{13} represents a hydrogen atom or an alkyl group of 1 to 20 carbon atoms, and X^1 and $X^{1'}$ each represents independently a hydrogen atom or a group capable of substitution on a benzene ring.

8. (original) A photothermographic material according to claim 7, wherein R¹¹ and R¹¹ in the general formula (R) each represents independently a secondary or tertiary alkyl group of 3 to 15 carbon atoms.

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9. (original) A photothermographic material according to claim 1, which further comprising a compound represented by the following general formula (H): General formula (H)

$$Q-(Y)_N-C(Z_1)(Z_2)X$$

in which Q represents an alkyl group, aryl group or heterocyclic group, Y represents a bivalent connection group, N represents 0 or 1, Z₁ and Z₂ each represents a halogen atom, and X represents a hydrogen atom or an electron attractive group.

10. (original) An image forming method for a photothermographic material which comprises exposing a photothermographic material according to claims 1 by using a semiconductor laser having an emission peak intensity at a wavelength of from 350 nm to 450 nm as a light source.

11. (cancelled)

- 12. (currently amended) A photothermographic material according to claim 1, wherein the average γ-phase ratio of the photosensitive silver halide is 5 mol% or more and to 90 mol% or less.
- 13. (currently amended) A photothermographic material according to claim 1, wherein the average γ-phase ratio of the photosensitive silver halide is 25 mol% or more and to 50 mol% or less.

14. (original) A photothermographic material according to claim 1, further comprising a compound in which a one-electron oxidant formed by one-electron oxidation can release one electron or more electrons.

15. (cancelled)

- 16. (currently amended) A photothermographic material according to claim 1, wherein the non-photosensitive organic silver salt contains silver behenate by in an amount of 65 mol% or more and to 85 mol% or less.
- 17. (original) A photothermographic material according to claim 1, further comprising a development accelerator.
- 18. (original) A photothermographic material according to claim 1, further comprising a compound represented by the following general formula (D): General formula (D)

in which R²¹ to R²³ each represents independently an alkyl group, aryl group, alkoxy group, aryloxy group, amino group or heterocyclic group.

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- 19. (original) An image forming method for a photothermographic material according to claim 10, wherein the exposure illuminance of the semiconductor laser is 1 mW/mm² or more.
- 20. (currently amended) An image forming method for the photothermographic material according to claim 10, wherein the exposure illuminance of the semiconductor laser is 10 mW/mm² or-more-and to 50 mW/mm² or less.